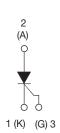


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Thyristor High Voltage, Phase Control SCR, 40 A





TO-247AC

PRIMARY CHARACTERISTICS						
I _{T(AV)} 35 A						
V _{DRM} /V _{RRM}	800 V, 1200 V					
V _{TM}	1.45 V					
I _{GT}	150 mA					
T _J	-40 °C to +125 °C					
Package	TO-247AC					
Circuit configuration	Single SCR					

FEATURES

- · Designed and qualified according to JEDEC®-JESD 47
- Low IGT parts available
- 125 °C max. operating junction temperature
- Material categorization: for definitions of compliance please see www.vishay.com/doc?99912





RoHS COMPLIANT **HALOGEN** FREE

APPLICATIONS

 Typical usage is in input rectification crowbar (soft start) and AC switch motor control, UPS, welding and battery charge

DESCRIPTION

The VS-40TPS... high voltage series of silicon controlled rectifiers are specifically designed for medium power switching and phase control applications. The glass passivation technology used has reliable operation up to 125 °C junction temperature.

MAJOR RATINGS AND CHARACTERISTICS							
PARAMETER	TEST CONDITIONS	VALUES	UNITS				
I _{T(AV)}	Sinusoidal waveform	35	Α Α				
I _{RMS}		55					
V _{RRM} /V _{DRM}		800/1200	V				
I _{TSM}		600	А				
V _T	40 A, T _J = 25 °C	1.45	V				
dV/dt		1000	V/µs				
dl/dt		100	A/µs				
T _J		-40 to +125	°C				

VOLTAGE RATINGS							
PART NUMBER	V _{RRM} /V _{DRM} , MAXIMUM REPETITIVE PEAK AND OFF-STATE VOLTAGE V	V _{RSM} , MAXIMUM NON-REPETITIVE PEAK REVERSE VOLTAGE V	I _{RRM} /I _{DRM} AT 125 °C mA				
VS-40TPS08APbF, VS-40TPS08A-M3	800	900					
VS-40TPS08PbF, VS-40TPS08-M3	800	900	10				
VS-40TPS12APbF, VS-40TPS12A-M3	1200	1300	10				
VS-40TPS12PbF, VS-40TPS12-M3	1200	1300					



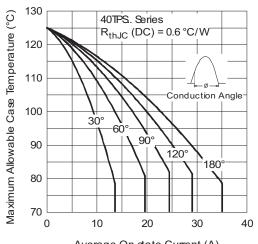
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ABSOLUTE MAXIMUM RATINGS						
PARAMETER	SYMBOL	TEST CONDITIONS			VALUES	UNITS
Maximum average on-state current	I _{T(AV)}	T _C = 79 °C, 180° con	duction half sine wave		35	
Maximum continuous RMS on-state current as AC switch	I _{T(RMS)}					Α
Maximum peak, one-cycle	L	10 ms sine pulse, rate	ed V _{RRM} applied		500	
non-repetitive surge current	I _{TSM}	10 ms sine pulse, no	voltage reapplied		600	
Maying up 12t fay fuaing	l ² t	10 ms sine pulse, rate	ed V _{RRM} applied	Initial $T_{.1} = T_{.1} \text{ max.}$	1250	A ² s
Maximum I ² t for fusing	1-1	10 ms sine pulse, no	voltage reapplied	rj = rjinax.	1760	
Maximum I²√t for fusing	I²√t	t = 0.1 ms to 10 ms, r	17 600	A²√s		
Low level value of threshold voltage	V _{T(TO)1}					V
High level value of threshold voltage	V _{T(TO)2}					V
Low level value of on-state slope resistance	r _{t1}					
High level value of on-state slope resistance	r _{t2}	1			7.50	mΩ
Maximum peak on-state voltage	V_{TM}	110 A, T _J = 25 °C			1.85	٧
Maximum rate of rise of turned-on current	dl/dt	T _J = 25 °C			100	A/μs
Maximum holding current	I _H	Anode supply = 6 V, r	esistive load, initial T _J	= 1 A, I _T = 25 °C	200	
Maximum latching current	ΙL	Anode supply = 6 V, resistive load, T _J = 25 °C			300	
		$T_{J} = 25 \text{ °C}$ $T_{J} = 125 \text{ °C}$ $V_{R} = \text{Rated V}_{RRM} / \text{V}_{DRM}$		0.5	mA	
Maximum reverse and direct leakage current	I _{RRM/} I _{DRM}			RM	10	1
Maximum rate of rise of off-state voltage 40TPS12A	ط/\//ط±				500	1////
Maximum rate of rise of off-state voltage 40TPS12	dV/dt	T_J = T_J maximum, linear to 80 % V_{DRM},R_g^- k = 100 Ω		1000	- V/μs	

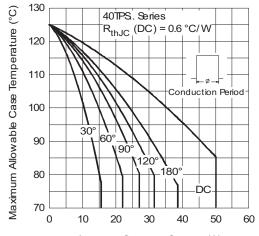
TRIGGERING					
PARAMETER	SYMBOL	TEST CO	TEST CONDITIONS		
Maximum peak gate power	P _{GM}			10	W
Maximum average gate power	P _{G(AV)}			2.5	VV
Maximum peak gate current	I _{GM}			2.5	Α
Maximum peak negative gate voltage	- V _{GM}			10	V
		T _J = - 40 °C		4.0	V
Maximum required DC gate voltage to trigger	V_{GT}	T _J = 25 °C	Anode supply = 6 V	2.5	
		T _J = 125 °C	- Tesistive load	1.7	
	l _{GT}	T _J = - 40 °C	Anode supply = 6 V	270	mA
Marian and in 100 and a small all from		T _J = 25 °C		150	
Maximum required DC gate current to trigger		T _J = 125 °C	- Tesistive load	80	
		T _J = 25 °C, for 40TPS08APbF and 40TPS12APbF		40	
Maximum DC gate voltage not to trigger for 40TPS12	V_{GD}	T _J = 125 °C, V _{DRM} = Rated value		0.25	V
Maximum DC gate current not to trigger for 40TPS12	I _{GD}			6	mA
Maximum DC gate voltage not to trigger for 40TPS12A	V_{GD}	T 405 °C V			V
Maximum DC gate current not to trigger for 40TPS12A	I _{GD}	T _J = 125 °C, V _{DRM} = Rated value		1	mA

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THERMAL AND MECHANICAL SPECIFICATIONS						
PARAMETER		SYMBOL	SYMBOL TEST CONDITIONS		UNITS	
Maximum junction and st temperature range	orage	T _J , T _{Stg}		-40 to +125	°C	
Maximum thermal resista junction to case	nce,	R _{thJC}	DC anavation	0.6		
Maximum thermal resista junction to ambient	nce,	R _{thJA}	DC operation	40	°C/W	
Maximum thermal resista case to heatsink	nce,	R _{thCS}	Mounting surface, smooth and greased	0.2		
Annyayinata waight				6	g	
Approximate weight				0.21	oz.	
Manustina taunus	minimum			6 (5)	kgf · cm	
Mounting torque	maximum			12 (10)	(lbf \cdot in)	
				40TP	S08A	
Mauldon desire					40TPS12A	
Marking device			Case style TO-247AC	40TF	PS08	
				40TF	PS12	



Average On-state Current (A)
Fig. 1 - Current Rating Characteristics



Average On-state Current (A)
Fig. 2 - Current Rating Characteristics





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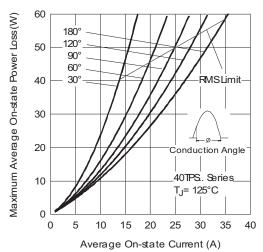
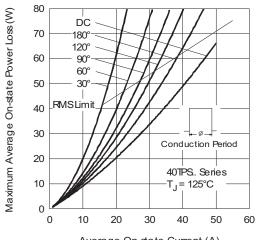


Fig. 3 - On-State Power Loss Characteristics



Average On-state Current (A)
Fig. 4 - On-State Power Loss Characteristics

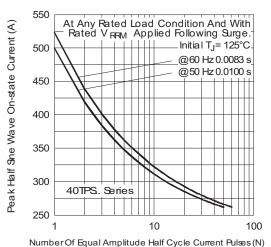


Fig. 5 - Maximum Non-Repetitive Surge Current

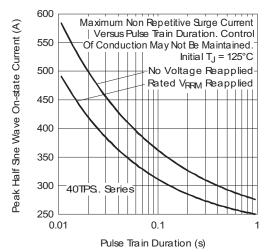


Fig. 6 - Maximum Non-Repetitive Surge Current

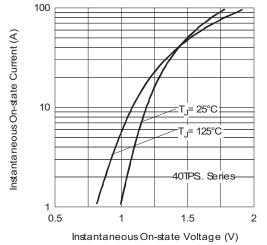


Fig. 7 - On-State Voltage Drop Characteristics

Instantaneous Gate Voltage (V)

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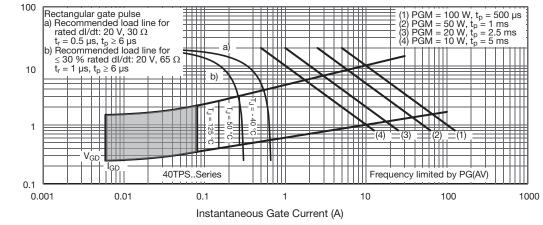


Fig. 8 - Gate Characteristics

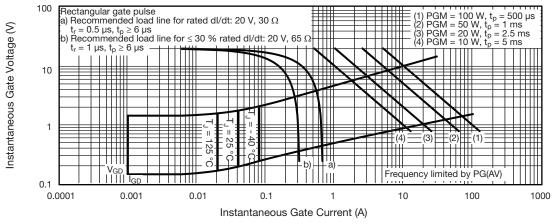


Fig. 9 - Gate Characteristics, 40TPS..A Series

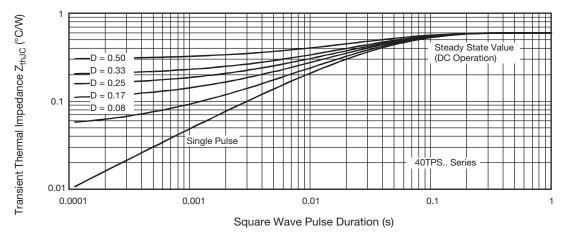
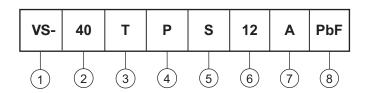


Fig. 10 - Thermal Impedance Z_{thJC} Characteristics

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ORDERING INFORMATION TABLE

Device code



1 - Vishay Semiconductors product

2 - Current rating (40 = 40 A)

3 - Circuit configuration:

T = Thyristor

4 - Package:

P = TO-247

5 - Type of silicon:

S = standard recovery rectifier

08 = 800 V 12 = 1200 V

6 - Voltage ratings

• A = low lgt selection 40 mA maximum

• None = standard lgt selection

8 - Environmental digit:

PbF = lead (Pb)-free and RoHS compliant

-M3 = halogen-free, RoHS compliant, and terminations lead (Pb)-free

ORDERING INFORMATION (Example)							
PREFERRED P/N	QUANTITY PER T/R	MINIMUM ORDER QUANTITY	PACKAGING DESCRIPTION				
VS-40TPS08APbF	25	500	Antistatic plastic tubes				
VS-40TPS08A-M3	25	500	Antistatic plastic tubes				
VS-40TPS08PbF	25	500	Antistatic plastic tubes				
VS-40TPS08-M3	25	500	Antistatic plastic tubes				
VS-40TPS12APbF	25	500	Antistatic plastic tubes				
VS-40TPS12A-M3	25	500	Antistatic plastic tubes				
VS-40TPS12PbF	25	500	Antistatic plastic tubes				
VS-40TPS12-M3	25	500	Antistatic plastic tubes				

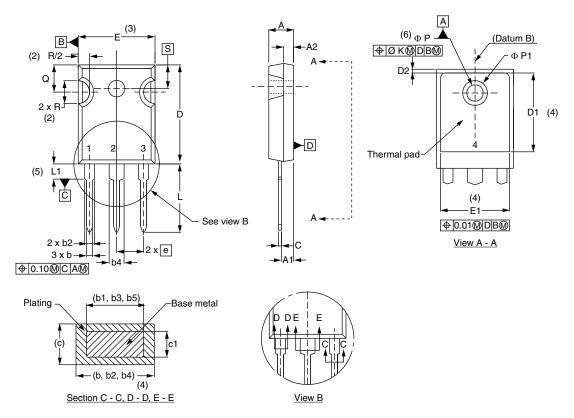
LINKS TO RELATED DOCUMENTS					
Dimensions <u>www.vishay.com/doc?95542</u>					
Down and the state was attach	TO-247AC PbF	www.vishay.com/doc?95226			
Part marking information	TO-247AC-M3	www.vishay.com/doc?95007			



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TO-247AC - 50 mils L/F

DIMENSIONS in millimeters and inches



SYMBOL	MILLIN	IETERS	INC	NOTES	
STWIBOL	MIN.	MAX.	MIN.	MAX.	NOTES
Α	4.65	5.31	0.183	0.209	
A1	2.21	2.59	0.087	0.102	
A2	1.17	1.37	0.046	0.054	
b	0.99	1.40	0.039	0.055	
b1	0.99	1.35	0.039	0.053	
b2	1.65	2.39	0.065	0.094	
b3	1.65	2.34	0.065	0.092	
b4	2.59	3.43	0.102	0.135	
b5	2.59	3.38	0.102	0.133	
С	0.38	0.89	0.015	0.035	
c1	0.38	0.84	0.015	0.033	
D	19.71	20.70	0.776	0.815	3
D1	13.08	-	0.515	-	4

SYMBOL	MILLIN	IETERS	INC	HES	NOTES
OTWIDOL	MIN.	MAX.	MIN.	MAX.	NOTES
D2	0.51	1.35	0.020	0.053	
Ш	15.29	15.87	0.602	0.625	3
E1	13.46	-	0.53	-	
е	5.46	BSC	0.215	BSC	
ØK	0.2	254	0.0)10	
L	14.20	16.10	0.559	0.634	
L1	3.71	4.29	0.146	0.169	
ØΡ	3.56	3.66	0.14	0.144	
Ø P1	-	7.39	-	0.291	
Q	5.31	5.69	0.209	0.224	
R	4.52	5.49	0.178	0.216	
S	5.51	BSC	0.217	BSC	

Notes

- (1) Dimensioning and tolerancing per ASME Y14.5M-1994
- (2) Contour of slot optional
- (3) Dimension D and E do not include mold flash. Mold flash shall not exceed 0.127 mm (0.005") per side. These dimensions are measured at the outermost extremes of the plastic body
- (4) Thermal pad contour optional with dimensions D1 and E1
- (5) Lead finish uncontrolled in L1
- (6) Ø P to have a maximum draft angle of 1.5 to the top of the part with a maximum hole diameter of 3.91 mm (0.154")
- (7) Outline conforms to JEDEC® outline TO-247 with exception of dimension c and Q



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